TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

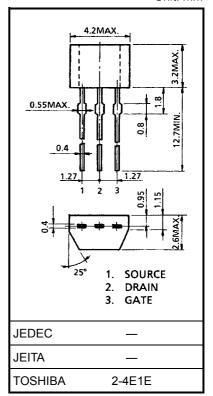
2SK1061

High Speed Switching Applications Analog Switch Applications Interface Applications

- Excellent switching times: ton = 14 ns (typ.)
- High forward transfer admittance: $|\,Y_{\rm fs}\,|$ = 100 mS (min)
- Low on resistance: R_{DS} (ON) = 0.6 Ω (typ.)
- Enhancement-mode
- Complementary to 2SJ167

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	I _D	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = 25° C)		PD	300	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



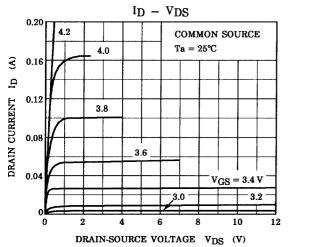
Weight: 0.13 g (typ.)

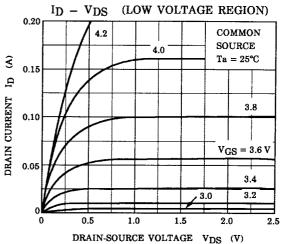
Electrical Characteristics (Ta = 25°C)

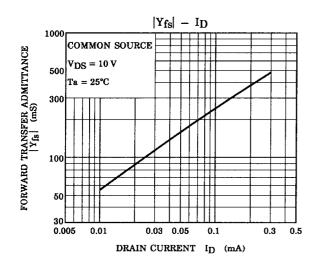
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 10~V,~V_{DS}=0$	_	_	±100	nA
Drain cut-off current		I _{DSS}	$V_{DS} = 60 V, V_{GS} = 0$	_	_	10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	60	_	_	V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2	—	3.5	V
Forward transfer admittance		Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ mA}$	100	—	—	mS
Drain-source ON	resistance	R _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		0.6	1.0	Ω
Drain-source ON voltage		V _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		30	50	mV
Input capacitance		C _{iss}			55	65	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$		13	18	pF
Output capacitance		C _{oss}			40	50	pF
Switching time	Rise time	tr	$ IO V \prod_{0} V_{IN} V_{IN} \downarrow^{ID} = 100 \text{ mA} $	_	8	_	- ns
	Turn-on time	t _{on}	$ \begin{array}{c} 0 & \downarrow & \downarrow & \vee IN \\ 10 & \mu s_{0} & \downarrow & \downarrow & \downarrow & \downarrow & \vee VOUT \\ 0 & \downarrow & \vee VOUT \\ 0 & \downarrow & $		14	_	
	Fall time	t _f		_	35	_	
	Turn-off Time	t _{off}	$\begin{array}{l} D.U. \leqq 1\% \\ V_{IN}: t_{f}, t_{f} < 5 \; ns \\ (Z_{out} = 50 \; \Omega) \end{array}$	_	75		

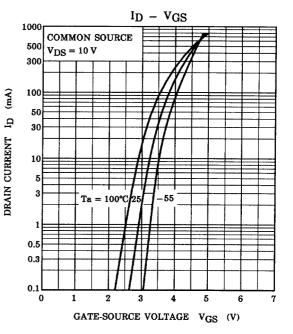
Note: This transistor is the electrostatic sensitive device. Please handle with caution.

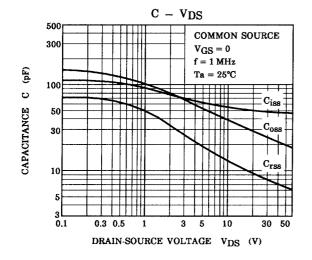
TOSHIBA



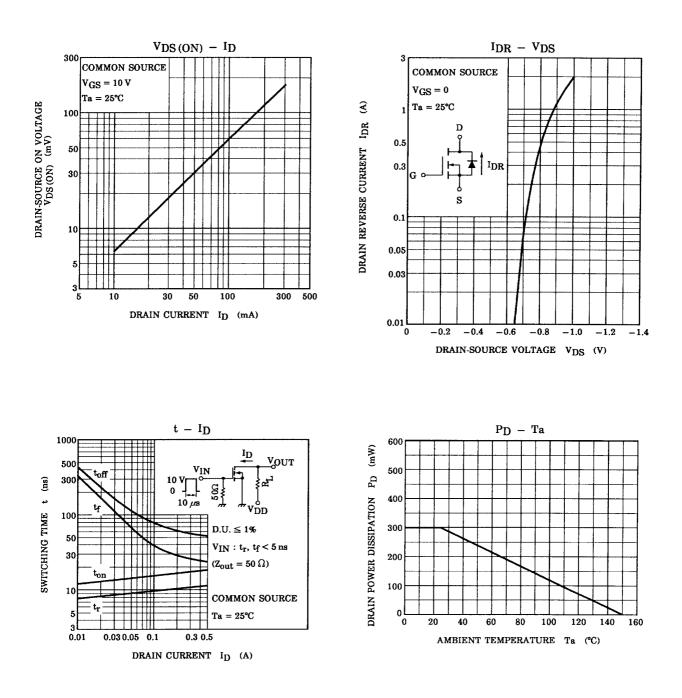








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